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APPLICANTS

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** CONTINUING DATA *****

This application is a CON of PCT/JP03/13747 10/28/2003

SWC

** FOREIGN APPLICATIONS *****

JAPAN 2002-318190 10/31/2002

JAPAN 2002-313902 10/29/2002

SWC

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** 06/23/2004

Foreign Priority claimed 35 USC 119 (a-d) conditions met	<input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance	STATE OR COUNTRY JAPAN	SHEETS DRAWING 14	TOTAL CLAIMS 19	INDEPENDENT CLAIMS 2
Verified and Acknowledged	Examiner's Signature <i>Asamira W. Suzuki</i> Initials <i>SWC</i>				

ADDRESS

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TITLE

Gallium indium nitride arsenide based epitaxial wafer, a hetero field effect transistor using the wafer,
 and a method of fabricating the hetero field effect transistor